

**AMENDMENTS TO THE CLAIMS**

1. (Currently Amended): A method for forming a pattern over a substrate, comprising:  
providing a master having at least one opening;  
providing a substrate having an etching layer formed thereon;  
locating the master over the etching layer the master having at least one opening;  
filling a resist in the at least one opening of the master; and  
separating ~~mechanically~~ the master from the substrate to leave the resist on the substrate,  
wherein the master is separately formed from the substrate so that the master is separable from the substrate.

2. (Original): The method of claim 1, wherein the filling a resist in the at least one opening of the master comprises:  
contacting a resist supplying roll to the master; and  
filling the resist in the at least one opening of the master by rotating the resist supplying roll over the at least one opening of the master.

3. (Original): The method of claim 1, wherein the filling a resist in the at least one opening of the master comprises:  
applying the resist on the master; and  
planarizing the applied resist on the surface of the master by using a doctor blade.

4. (Original): The method of claim 1, wherein the master is separated apart from the substrate by a few micrometers ( $\mu\text{m}$ ).

5. (Original): The method of claim 1, wherein the etching layer is a metal layer.

6. (Original): The method of claim 1, wherein the etching layer is an insulating layer.

7. (Original): The method of claim 6, wherein the insulating layer is formed of one of SiO<sub>x</sub> or SiN<sub>x</sub>.

8. (Original): The method of claim 1, wherein the etching layer is a semiconductor layer.

9. (Original): The method of claim 1, further comprising hardening the resist.

10. (Currently Amended): A method for forming a pattern over a substrate, comprising:

providing a master having at least one opening;

providing a substrate having an etching layer formed thereon;

placing the master over an area corresponding to the etching layer to be etched;

applying a resist on the master;

planarizing the applied resist on the surface of the master and filling the resist in the at least one opening by using a doctor blade;

hardening the planarized resist; and

forming a resist pattern on the etching layer by separating ~~mechanically~~ the master from the substrate,

wherein the master is separately formed from the substrate so that the master is separable from the substrate.

11. The method of claim 10, wherein the master is separated apart from the substrate by a few micrometers ( $\mu\text{m}$ ).

12. (Currently Amended): A method for forming a pattern over a substrate, comprising:

providing a master having at least one opening

providing a substrate having an etching layer formed thereon;

placing the master over the etching layer, the opening of the master being corresponding to the etching region to be etched;

contacting a resist supplying roll on the master to fill the resist in the at least one opening of the master;

hardening the filled resist in the at least one opening of the master; and

forming a resist pattern on the etching layer by separating mechanically the master from the substrate,

wherein the master is separately formed from the substrate so that the master is separable from the substrate.

13. The method of claim 12, wherein the master is separated apart from the substrate by a few micrometers ( $\mu\text{m}$ ).